

Enhanced ultrafast power diode

24 August 2018

**Product data sheet** 

# 1. General description

Enhanced ultrafast power diode in a SOT404 (D2PAK) plastic package

## 2. Features and benefits

- High thermal cycling performance
- Low on-state losses
- Low thermal resistance
- Soft recovery characteristic
- Surface-mountable package

## 3. Applications

- Dual Mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

# 4. Quick reference data

Fable 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta = 0.5$ ; T <sub>mb</sub> $\leq 126$ °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	5	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_{p}$ = 25 µs; $T_{mb}$ ≤ 126 °C; SQW	-	-	10	A
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 3</u>	-	-	60	А
	forward current	t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 3</u>	-	-	66	А
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.3	1.9	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.1	1.7	V
Dynamic ch	naracteristics	·		·		
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 6</u>	-	17.5	35	ns

### 5. Pinning information

Table 2.	able 2. Pinning information						
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	n.c.	not connected	mb	K — A 001aaa020			
2	К	cathode[1]		001aaa020			
3	А	anode					
mb	mb	mounting base; cathode					
			D2PAK (SOT404)				

[1] It is not possible to connect to pin 2 of the SOT404 package.

# 6. Ordering information

# Table 3. Ordering information Type number Package Name Description Version BYV25FB-600 D2PAK plastic single-ended surface-mounted package (D2PAK); 3 SOT404

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## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>mb</sub> ≤ 126 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	5	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 126 °C; SQW	-	10	A
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 3</u>	-	60	А
	forward current	t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 3</u>	-	66	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

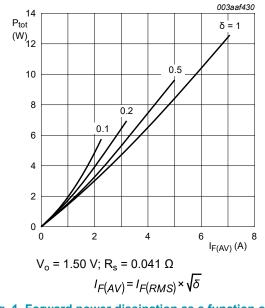


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

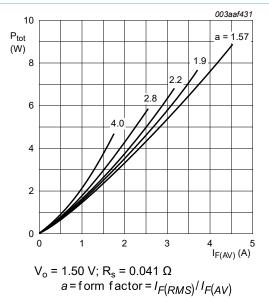
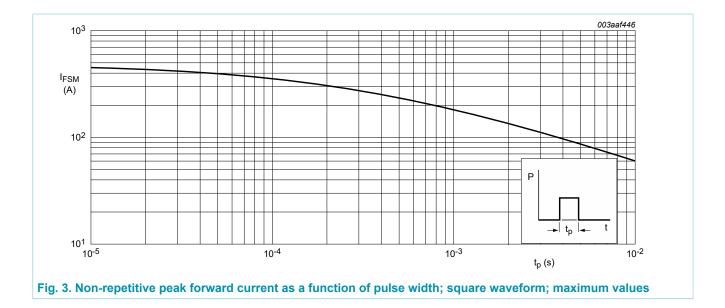


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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# BYV25FB-600

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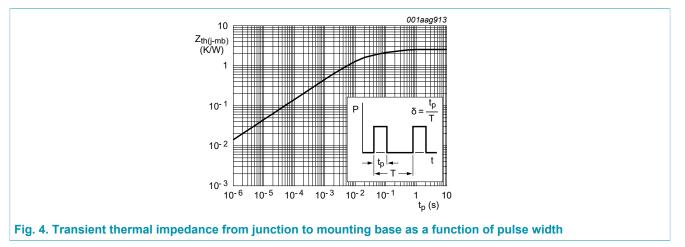


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#### 8. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4		-	-	2.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	[1]	-	50	-	K/W

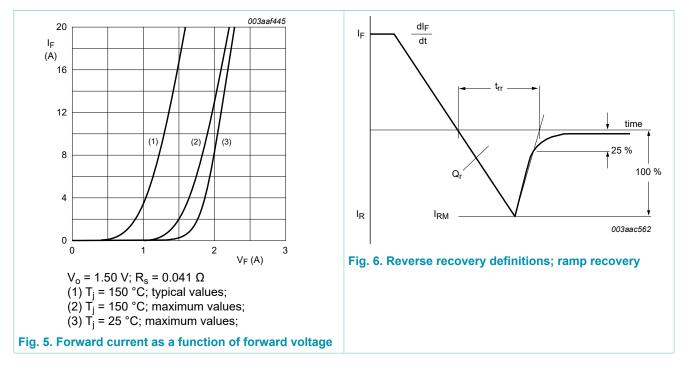
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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### 9. Characteristics

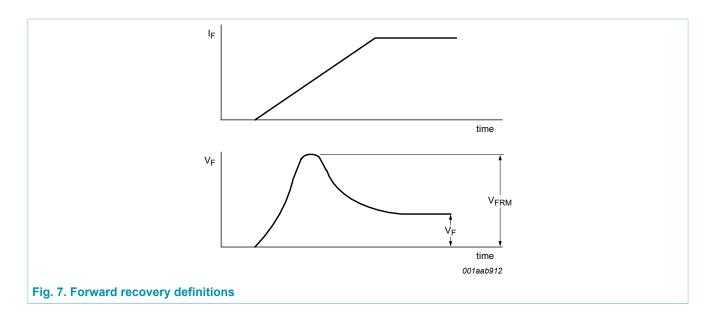
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				-
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.3	1.9	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.1	1.7	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C	-	-	1.5	mA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	50	μA
Dynamic ch	naracteristics		·			
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A};  V_R = 30  \text{V};  \text{d} I_F/\text{d} t = 100  \text{A}/\mu\text{s}; \\ T_j = 25 ^\circ\text{C}; \frac{\text{Fig. 6}}{2}$	-	17.5	35	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A};  \text{V}_\text{R} = 30  \text{V};  \text{d}_\text{F}/\text{d}\text{t} = 100  \text{A}/\mu\text{s}; \\ \text{T}_j = 25 ^\circ\text{C}$	-	1.5	-	A
Q <sub>r</sub>	recovered charge		-	13	-	nC
V <sub>FR</sub>	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; Fig. 7	-	3.2	-	V



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## 10. Package outline

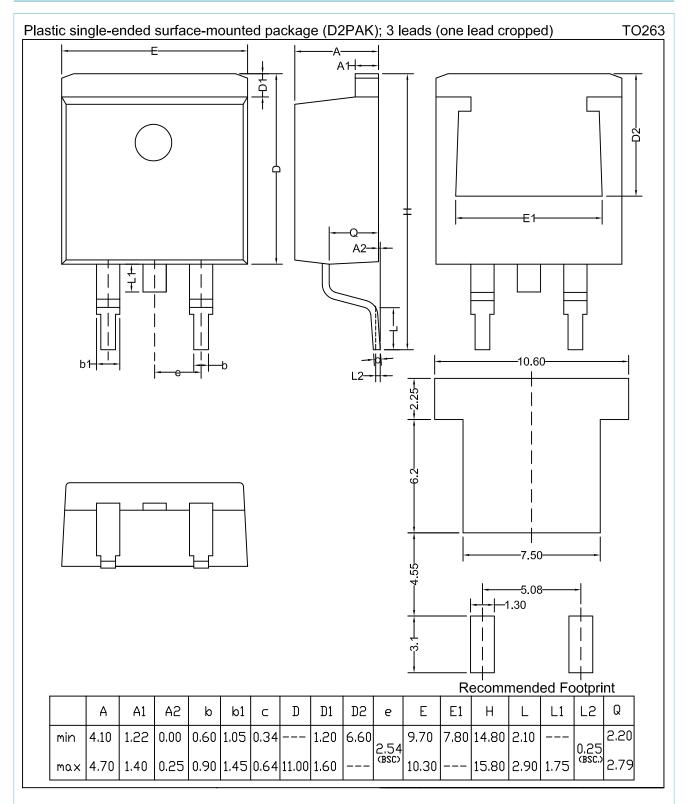


Fig. 8. Package outline D2PAK (SOT404)

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#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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